

N-Ch MOSFET

General Description

The WST6006 is the highest performance trench N-CH MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST6006 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- High-speed switching
- Green Device Available
- ESD Protected:2KV

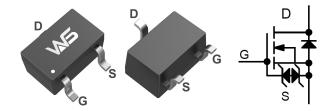
Product Summery

BVDSS	RDSON	ID
60V	1.4Ω	115mA

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC
- Networking DC-DC Power System
- Load Switch

SOT-323 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	115	mA
I _D @T _A =70℃	Continuous Drain Current, V _{GS} @ 10V ¹	75	mA
I _{DM}	Pulsed Drain Current ²	1.0	А
P₀@T _A =25℃	Total Power Dissipation ³	0.2	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹		625	°C/W



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Electrical Characteristics (T_J=25 $^{\circ}$ C, unless otherwise noted)

Symbol	Parameter	Conditions		Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage V _{GS} =0V , I _D =250uA		60			V	
$\triangle BV_{DSS} / \triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$, I_D=1mA		0.05		V/℃	
Б	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =0.5A		1.4	7.5		
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =5V , I _D =0.05A		10.5	13.5	Ω	
V _{GS(th)}	Gate Threshold Voltage		1	1.6	2.5	V	
	V _{GS(th)} Temperature Coefficient	─V _{GS} =V _{DS} , I _D =250uA		-3.7		mV/℃	
		V_{DS} =60V , V_{GS} =0V , TJ=25 $^\circ\!\!\mathbb{C}$			1		
I _{DSS}	Drain-Source Leakage Current	V_{DS} =60V , V_{GS} =0V , TJ=55 $^\circ\!\!\mathrm{C}$			5	u A	
I _{GSS}	Gate-Source Leakage Current $V_{GS}=\pm 20V$, $V_{DS}=0V$				±10	uA	
gfs	Forward Transconductance VDS≥ 2.0 VDS(on), ID = 200 mAdc)			80		mS	
T _{d(on)}	Turn-On Delay Time			7	6		
Tr	Rise Time (VDD = 25 Vdc , ID =500			1.8	3.3		
T _{d(off)}	Turn-Off Delay Time	mAdc, RG = 25 ,RL = 50 ,Vgen = 10 V)		11	40	ns	
T _f	Fall Time	,,		6.8	13.6		
C _{iss}	Input Capacitance			17	50		
C _{oss}	Output Capacitance VDS = 25 Vdc, VGS = 0, f = 1.0 MHz			10	25	pF	
C _{rss}	Reverse Transfer Capacitance			2.5	5.0		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}				115	mA
I _{SM}	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			800	mA
V _{SD}	Diode Forward Voltage ²	IS = 115 mAdc, VGS = 0 V			1.5	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%

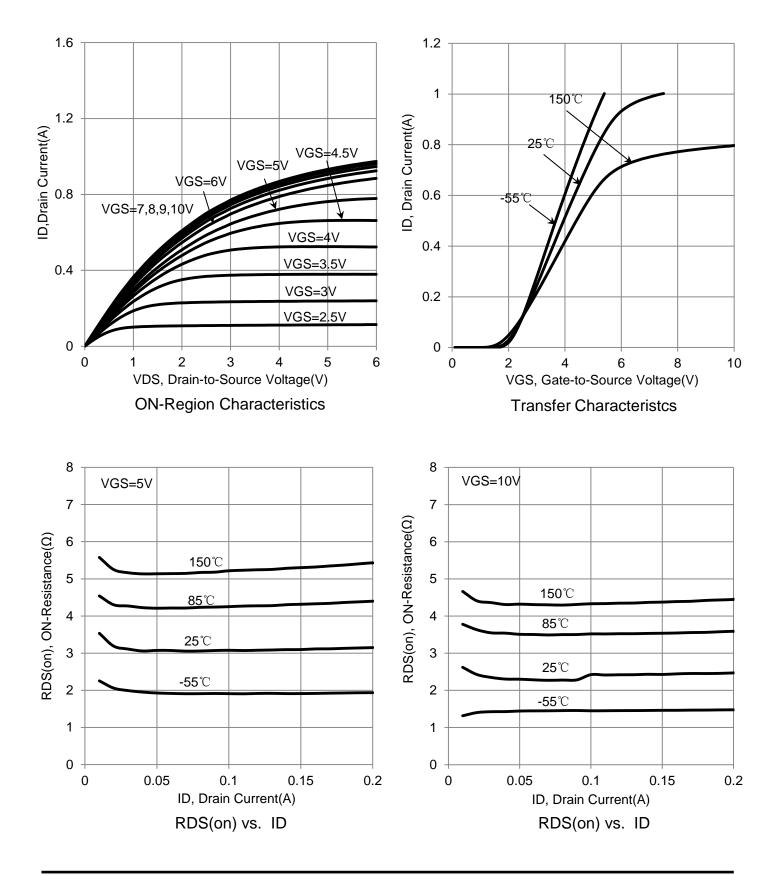
3.The power dissipation is limited by 150 $^\circ\!\mathrm{C}$ junction temperature.

4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



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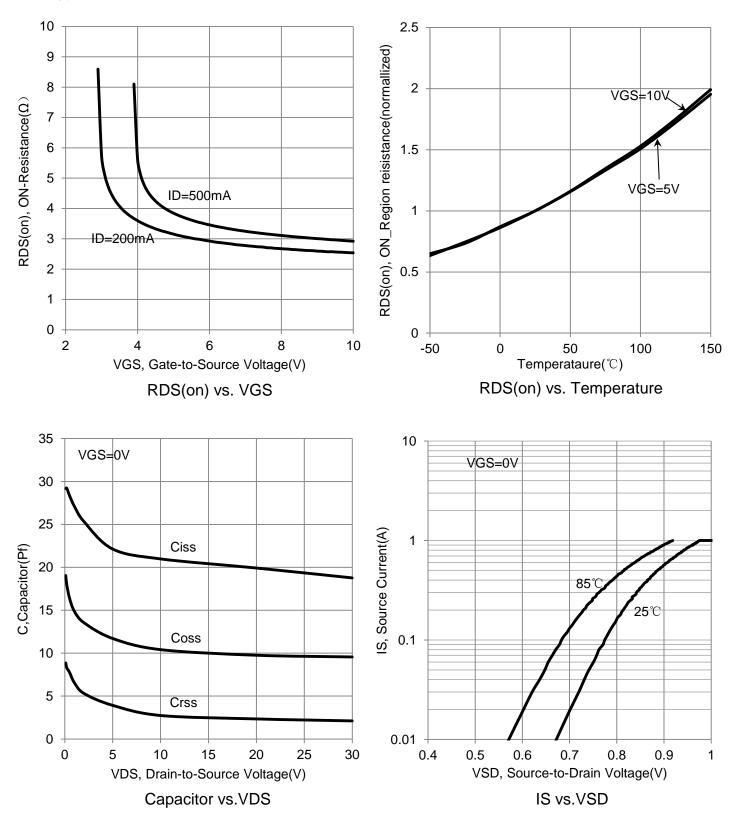
Typical Characteristics





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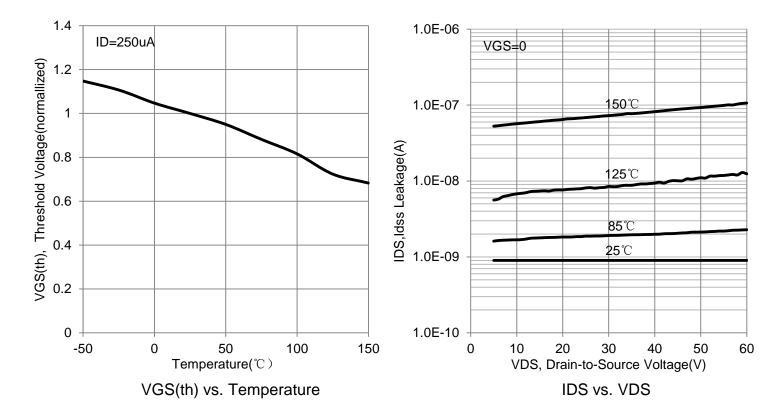
Typical Characteristics





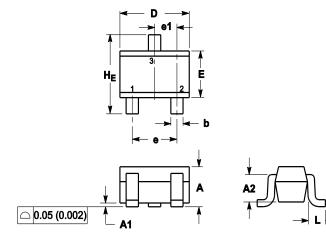
N-Ch MOSFET

Typical Characteristics



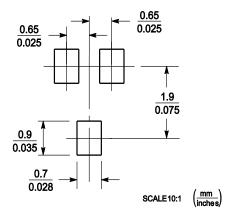


OUTLINE AND DIMENSIONS



	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
А	0.80	0.90	1.00	0.032	0.035	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70REF			0.028REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Е	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65REF			0.026REF		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

SOLDERING FOOTPRINT





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